HFZT

SCS210AJ

SiC Schottky Barrier Diode

VOLTAGE RANGE: 650V

Features

- Shorter recovery time
- Reduced temperature dependence
- High-speed switching possible
- High surge current capability

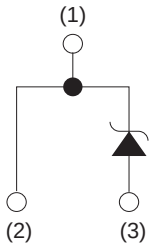
MECHANICAL DATA

- Case style:TO-220ACP molded plastic
- Mounting position:any

Outline

TO-220ACP

●Inner circuit



(1) Cathode
(2) Cathode
(3) Anode

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter		Symbol	Value	Unit
Reverse voltage (repetitive peak)		V_{RM}	650	V
Reverse voltage (DC)		V_R	650	V
Continuous forward current (T_c= 135°C)		I_F	10	A
Surge non-repetitive forward current	PW=10ms sinusoidal, T_j=25°C	I_{FSM}	82	A
	PW=10ms sinusoidal, T_j=150°C		69	A
	PW=10μs square, T_j=25°C		300	A
Repetitive peak forward current		I_{FRM}	45 *1	A
i^2t value	1≦PW≦10ms, T_j=25°C	$\int i^2dt$	33	A^2s
	1≦PW≦10ms, T_j=150°C		23	A^2s
Total power disspation		P_D	71 *2	W
Junction temperature		T_j	175	°C
Range of storage temperature		T_{stg}	−55 to +175	°C

*1 T_c=100°C, T_j=150°C, Duty cycle=10% *2 T_c=25°C

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RATINGS AND CHARACTERISTIC CURVES

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
DC blocking voltage	V_{DC}	I_R =50μA	650	-	-	V
Forward voltage	V_F	I_F=10A, T_j=25°C	-	1.35	1.50	V
		I_F=10A, T_j=150°C	-	1.44	1.71	V
		I_F=10A, T_j=175°C	-	1.50	-	V
Reverse current	I_R	V_R=650V, T_j=25°C	-	0.03	50	μA
		V_R=650V, T_j=150°C	-	2	200	μA
		V_R=650V, T_j=175°C	-	6	-	μA
Total capacitance	C	V_R=1V, f=1MHz	-	500	-	pF
		V_R=650V, f=1MHz	-	46	-	pF
Total capacitive charge	Q_C	V_R=400V, di/dt=350A/μs	-	24	-	nC
Switching time	t_C	V_R=400V, di/dt=350A/μs	-	15	-	ns
Non-repetetive Avaranche Energy	E_{ava}	L=1mH	-	130	-	mJ

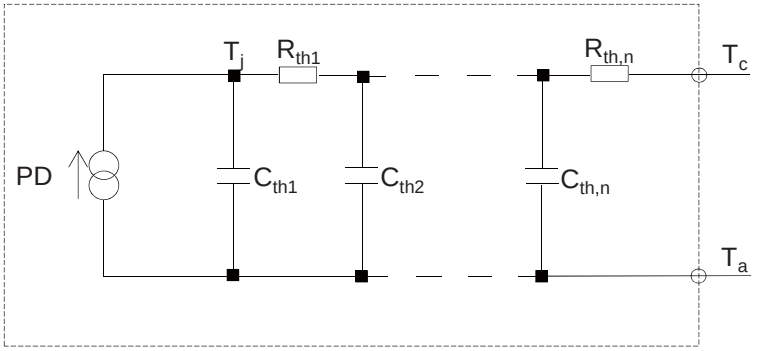
●Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance	$R_{th(j-c)}$	-	-	1.5	2.1	°C/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R_{th1}	1.55E-02	K/W
R_{th2}	1.46E-01	
R_{th3}	1.32E+00	

Symbol	Value	Unit
C_{th1}	2.63E-04	Ws/K
C_{th2}	1.00E-03	
C_{th3}	2.13E-03	



RATINGS AND CHARACTERISTIC CURVES

Electrical characteristic curves

Fig.1 V_F - I_F Characteristics

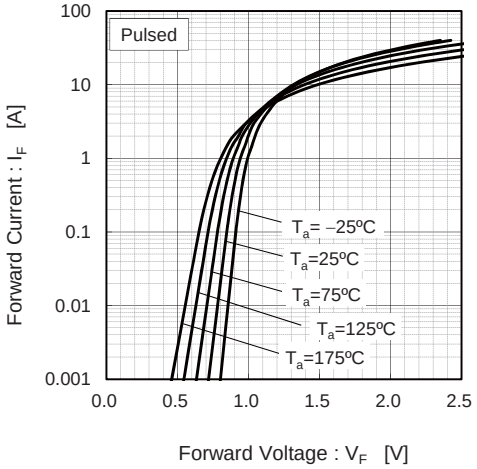


Fig.2 V_F - I_F Characteristics

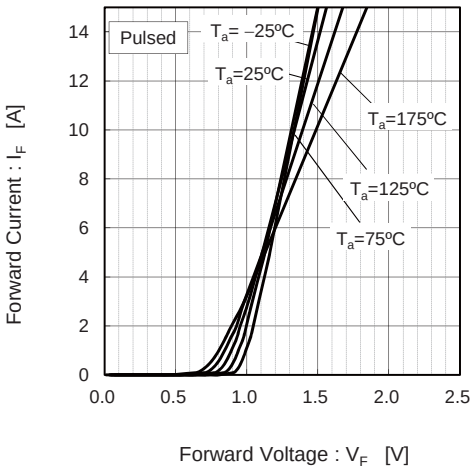


Fig.3 V_R - I_R Characteristics

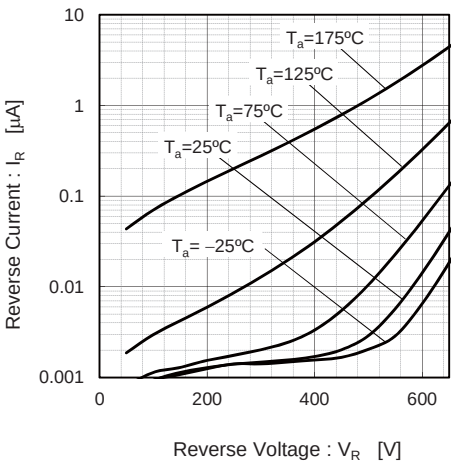


Fig.4 V_R-C_t Characteristics

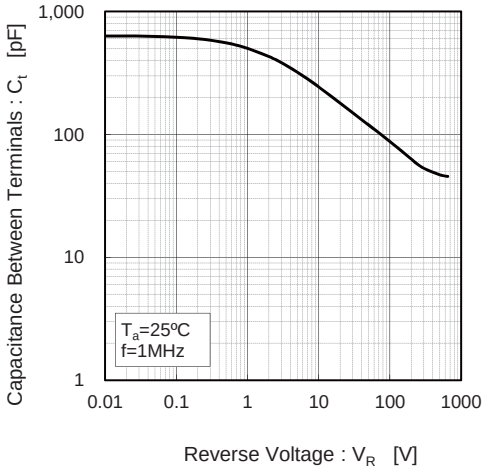


Fig.5 Typical Transient Thermal Resistance vs. Pulse Width

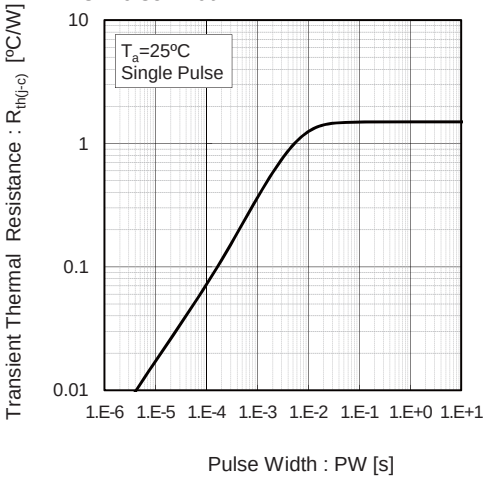


Fig.6 Power Dissipation

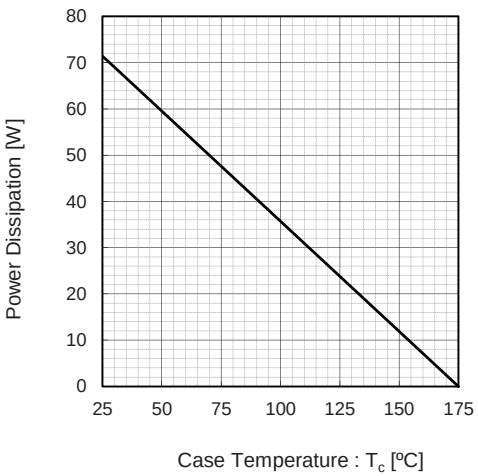
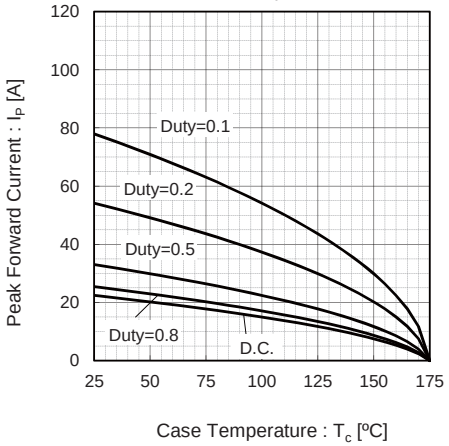
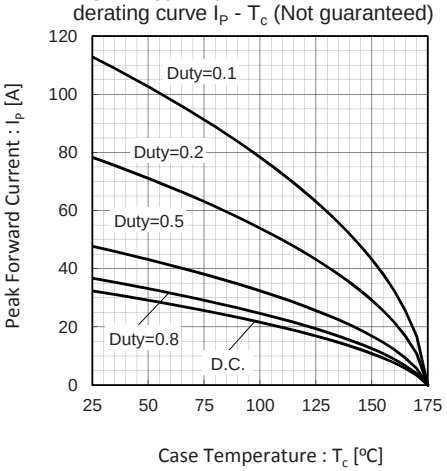


Fig.7*3 Maximum peak forward current derating curve I_P - T_c



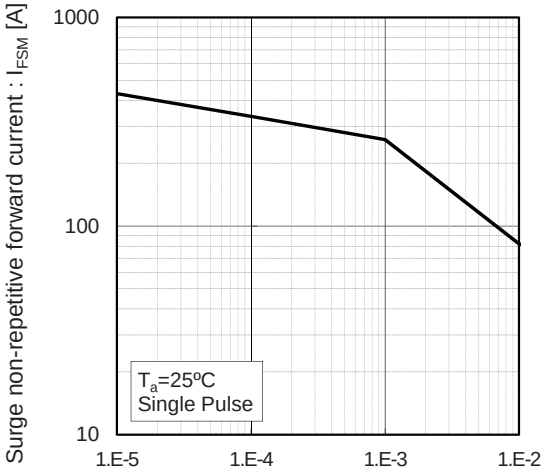
*3 Based on max Vf, max $R_{th(j-c)}$
Valid for switching of above 10kHz, excluding D.C. curve.

Fig.8*4 Typical peak forward current derating curve I_P - T_c (Not guaranteed)



*4 Based on typ Vf, typ $R_{th(j-c)}$
Typical value, not guaranteed
Valid for switching of above 10kHz, excluding D.C. curve

Fig.9 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)



RATINGS AND CHARACTERISTIC CURVES

Electrical characteristic curves

Fig.10 Typical capacitance store energy

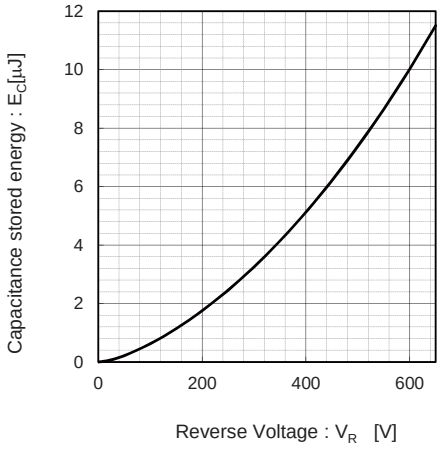
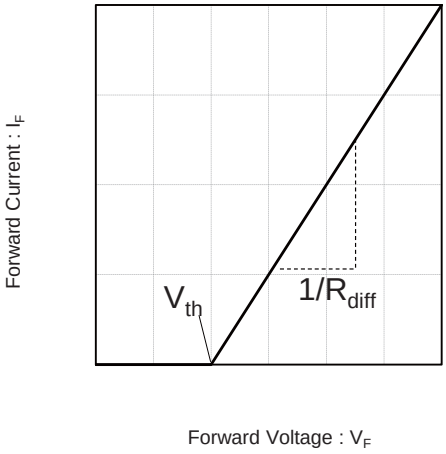


Fig.11 Equivalent forward current curve



$$V_F = V_{th} + R_{diff} I_F$$

$$V_{th}(T_j) = a_0 + a_1 T_j$$

$$R_{diff}(T_j) = b_0 + b_1 T_j + b_2 T_j^2$$

Symbol	Typical Value	Unit
a_0	9.66E-01	V
a_1	-1.10E-03	V/°C
b_0	3.52E-02	Ω
b_1	7.46E-05	Ω/°C
b_2	7.68E-07	$\Omega/°C^2$

T_j in ºC; -55 ºC < T_j <175 ºC ; I_F < 20A